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## SEMICONDUCTOR COMPONENT

## Cross-Reference to Related Application:

This application is a continuation of copending International Application No. PCT/DE00/01251, filed April 20, 2000, which designated the United States.

## Background of the Invention:

## Field of the Invention:

The invention relates to a voltage-controlled semiconductor component in which a high voltage is present between the terminals forming the load path.

The costs in the manufacture of a grid power supply constitute a fundamental problem. Suitable selection of a grid power supply is dependent on the application, just like the components that are intended to be used. Switched-mode grid power supplies, in particular, are being used more and more often. This is due, inter alia, to the fact that many complex circuit configuration of a switched-mode power supply can be combined on a single integrated semiconductor chip. This enables cost-effective manufacture. A semiconductor chip of this type has, in particular, a power switching device and a drive configuration for the power switching device. In this case, the load terminals of the power switching device are